

Search Notes

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	328	(438/384).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/24 23:29
S1	14	resistive adj elements same doping and anneal\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/19 15:55
S2	310	(438/382).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/19 18:37
S4	573	(438/385).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/19 19:09
S5	573	S4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 18:38
S6	108	S4 and dop\$3 and anneal\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 18:39
S7	22	S4 and dop\$3 and anneal\$3 and (electron or ion) adj beam	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 18:57
S8	43	S4 and dop\$3 and anneal\$3 and plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 18:40
S9	11	S7 and S8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 18:40

S10	7	S7 and S8 and pattern	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 18:53
S11	7	S4 and electrostatic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 19:11
S12	21	S2 and electrostatic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 19:13
S13	4	S2 and electrostatic and laser and (ion or electron)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 19:12
S14	23448	laser with discharge	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 19:14
S15	70	laser with discharge and resistor and dop\$3 and anneal\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 19:15
S16	57	laser with discharge and resistor and dop\$3 and anneal\$3 and pattern	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 19:15
S17	56	laser with discharge and resistor and dop\$3 and anneal\$3 and pattern and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 19:15
S18	48	laser with discharge and resistor and dop\$3 and anneal\$3 and pattern and semiconductor and plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 19:15
S19	127	resist\$3 and doping and anneal\$3 and boron same absorb\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:07

S20	47	resist\$3 and doping and anneal\$3 and boron same absorb\$4 and plasma and laser	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/24 09:06
S21	11	resist\$3 and doping and anneal\$3 and boron same absorb\$4 and plasma and laser and ion adj beam	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:10
S22	6	resistor and doping and anneal\$3 and boron same absorb\$4 and plasma and laser and ion adj beam	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:48
S23	8	resistor and doping and anneal\$3 and boron same absorb\$4 and plasma and ion adj beam	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 16:52
S24	2	("6358809").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/20 17:02
S25	2871	resistor and charg\$3 and dop\$3 and plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 17:03
S26	0	resistor and charg\$3 with e-beam and dop\$3 and plasma and anneal\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 17:03
S27	204	resistor and e-beam and dop\$3 and plasma and anneal\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 17:04
S28	154	resistor and e-beam and dop\$3 and plasma and anneal\$3 and laser	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 17:12
S29	310	(438/382).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/20 17:12

S30	0	resistor and e-beam and dop\$3 and plasma and anneal\$3 and laser and S29	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 17:12
S31	4	resistor and e-beam and dop\$3 and S29	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 17:16
S32	573	(438/385).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/20 17:16
S33	6	resistor and e-beam and dop\$3 and (S29 or S32)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 17:17
S34	14	resistor and (e-beam or (ion adj beam)) and plasma and dop\$3 and (S29 or S32)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/20 17:17
S35	15	resistor and doping and anneal\$3 and boron same absorb\$4 and plasma and laser	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/24 09:06
S36	23	"167851"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/26 18:47
S37	24	"0167851"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/26 18:49
S41	5	moksvold-tor-\$.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/19 17:31
S42	11	"4560583"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/26 19:11

S43	0	resistor and boron adj hexafluoride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/26 19:12
S44	0	resistor and boron adj hexafluoride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/26 19:12
S45	453	resistor same boron and anneal\$3 and dop\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/26 19:17
S46	296	resistor same boron same dop\$3 and anneal\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/26 19:17
S47	17	resistor same boron same dop\$3 same plasma and anneal\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/26 19:24
S48	102	resistor same dop\$3 same plasma and anneal\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/26 19:24
S49	81	GRIS-YVON.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/19 15:55
S50	2	GRIS-YVON.in. and resistive adj element	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/19 15:57
S51	21	GRIS-YVON.in. and resist\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/19 15:57
S52	10741	charg\$3 and dop\$3 and resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 18:42

S53	1365	charg\$3 and dop\$3 and resistor and anneal\$3 and plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/19 17:33
S54	37	charg\$3 and dop\$3 and resistor and anneal\$3 and plasma and ion with absorb\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/19 17:33
S55	1682	plasma adj doping	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/20 19:18
S56	192	plasma adj doping and resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/20 19:18
S57	10	plasma adj doping same resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/20 19:28
S58	2	"6358809"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/20 19:29
S59	2780	charg\$3 and dop\$3 and resistor and anneal\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 18:42
S60	1830	plasma adj doping	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 18:42
S61	118	charg\$3 and dop\$3 and resistor and anneal\$3 and S60	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 18:42
S62	67	charg\$3 and dop\$3 and resistor and anneal\$3 and S60 and electron adj beam	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 18:43

S63	8	charg\$3 and dop\$3 and resistor and anneal\$3 and S60 and ion adj beam	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 18:50
S64	81781	charg\$3 same resistor dop\$3 and anneal\$3 and S60 and ion adj beam	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 18:50
S65	81692	charg\$3 same resistor anddop\$3 and anneal\$3 and S60 and ion adj beam	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 18:50
S66	2	charg\$3 same resistor and dop\$3 and anneal\$3 and S60 and ion adj beam	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 18:55
S67	14534	electron adj beam same charg\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 18:56
S68	2024	electron adj beam same charg\$3 and ion and plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 18:56
S69	63	electron adj beam same charg\$3 and ion and plasma with dop\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 19:35
S70	16	electron adj beam same charg\$3 and ion and plasma with dop\$3 and anneal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 18:56
S71	83	"5,645,897"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 19:35